

MC74VHC1G01

Single 2-Input NAND Gate with Open Drain Output

The MC74VHC1G01 is an advanced high speed CMOS 2-input NAND gate with an open drain output fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including an open drain output which provides the ability to set output switching level. This allows the MC74VHC1G01 to be used to interface 5 V circuits to circuits of any voltage between V_{CC} and 7 V using an external resistor and power supply.

The MC74VHC1G01 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage.

Features

- High Speed: $t_{PD} = 3.7$ ns (Typ) at $V_{CC} = 5$ V
- Low Internal Power Dissipation: $I_{CC} = 1$ μ A (Max) at $T_A = 25^\circ$ C
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

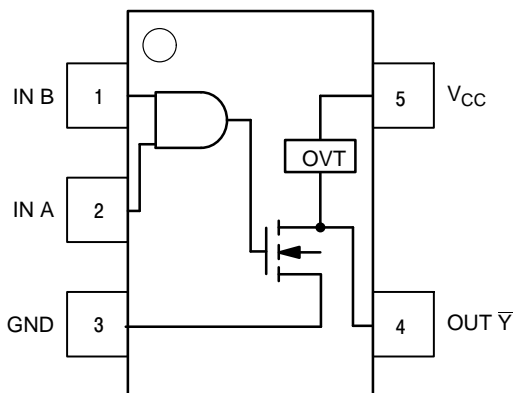


Figure 1. Pinout (Top View)

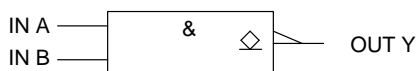


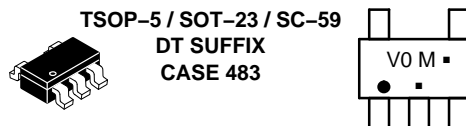
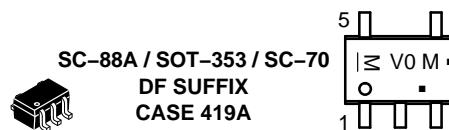
Figure 2. Logic Symbol



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



V0 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	IN B
2	IN A
3	GND
4	OUT \bar{Y}
5	V_{CC}

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHC1G01

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND; V _{OUT} > V _{CC}	±20
I _{OUT}	DC Output Sink Current, per Pin	25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pin	±25	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	+150	°C
θ _{JA}	Thermal Resistance	SC70-5/SC-88A (Note 1) TSOP-5	350 230
P _D	Power Dissipation in Still Air at 85°C	SC70-5/SC-88A TSOP-5	150 200
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±500

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage	0.0	5.5	V
V _{OUT}	DC Output Voltage	0.0	7.0	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.3 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V	0 100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

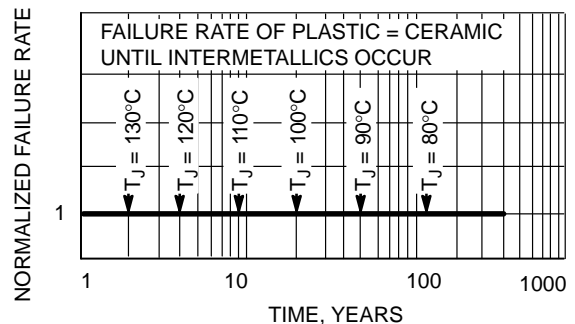


Figure 3. Failure Rate vs. Time Junction Temperature

MC74VHC1G01

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85	V	
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36	0.44 0.44		0.52 0.52		
I _{LKG}	Z-State Output Leakage Current	V _{IN} = V _{IL} V _{OUT} = V _{CC} or GND	5.5			±5		±10		±10	μA
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			1.0		20		40	μA
I _{OFF}	Power Off-Output Leakage Current	V _{OUT} = 5.5 V V _{IN} = 5.5 V	0			0.25		2.5		5	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS Input t_r = t_f = 3.0 ns

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55 ≤ T _A ≤ 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{pZL}	Maximum Output Enable Time, Input A or B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF R _L = R _I = 500 Ω C _L = 50 pF		5.5 8.0	7.9 11.4		9.5 13.0		11.0 15.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF R _L = R _I = 500 Ω C _L = 50 pF		3.7 5.2	5.5 7.5		6.5 8.5		8.0 10.0	
t _{PLZ}	Maximum Output Disable Time	V _{CC} = 3.3 ± 0.3 V C _L = 50 pF R _L = R _I = 500 Ω		8.0	11.4		13.0		15.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 50 pF R _L = R _I = 500 Ω		5.2	7.5		8.5		10.0	
C _{IN}	Maximum Input Capacitance			4	10		10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 6)	Typical @ 25°C, V_{CC} = 5.0V	pF
		18	

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

MC74VHC1G01

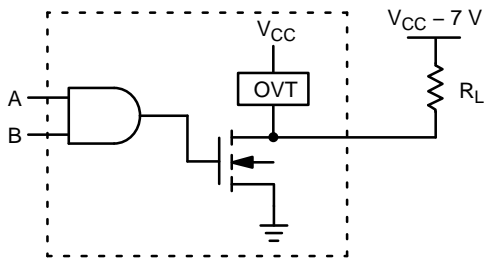


Figure 4. Output Voltage Mismatch Application

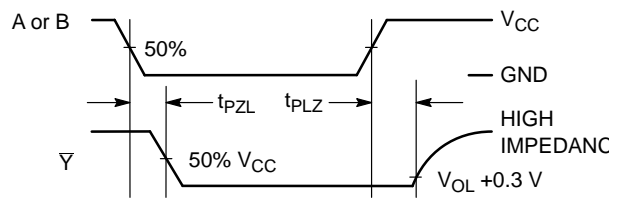
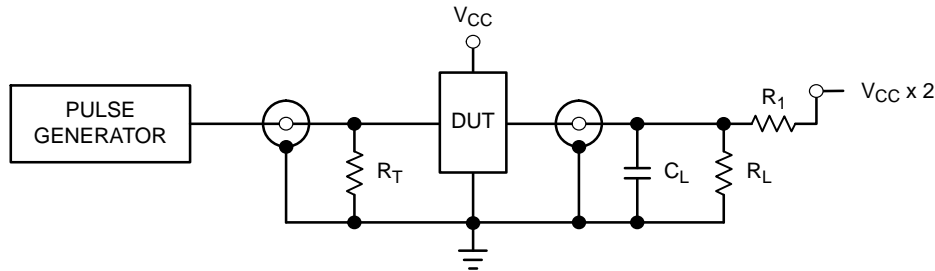
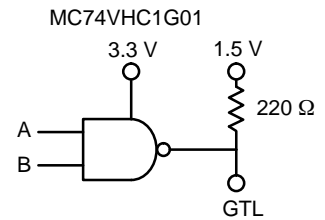
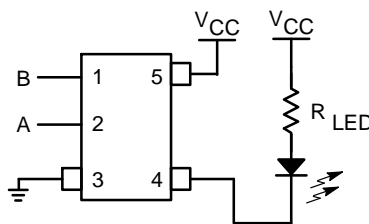
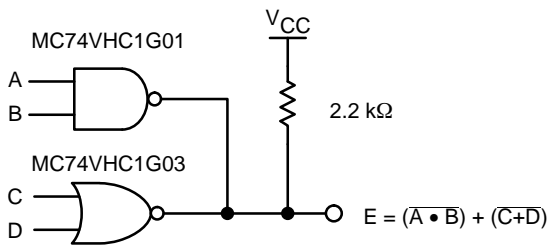


Figure 5. Switching Waveforms



$C_L = 50 \text{ pF}$ equivalent (Includes jig and probe capacitance)
 $R_L = R_1 = 500 \Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 6. Test Circuit



ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC1G01DFT1G	SC-88A / SC70-5 / SOT-353 (Pb-Free)	3000 Units / Tape & Reel
NLV74VHC1G01DFT1G*		
MC74VHC1G01DFT2G		
MC74VHC1G01DTT1G	TSOP-5 / SOT23-5 / SC59-5 (Pb-Free)	3000 Units / Tape & Reel
NLV74VHC1G01DTT1G*		

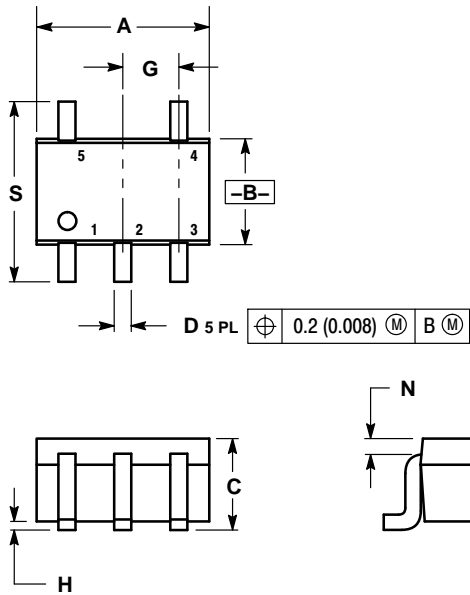
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MC74VHC1G01

PACKAGE DIMENSIONS

SC-88A
CASE 419A-02
ISSUE L

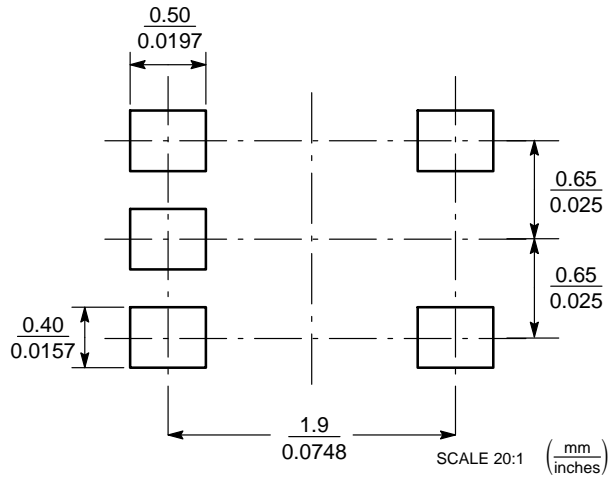


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

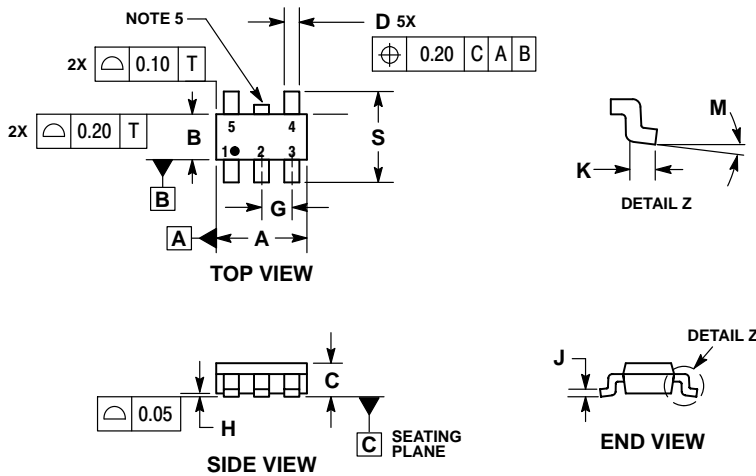
SOLDER FOOTPRINT



MC74VHC1G01

PACKAGE DIMENSIONS

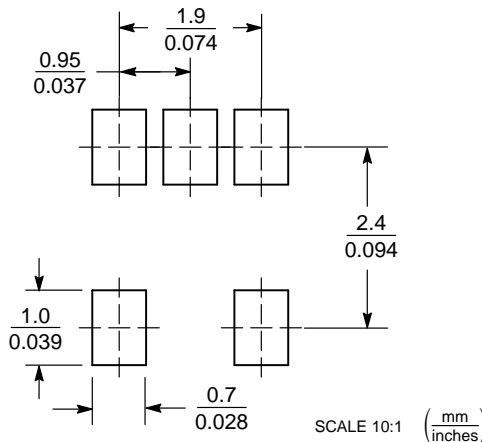
TSOP-5 CASE 483-02 ISSUE M



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative